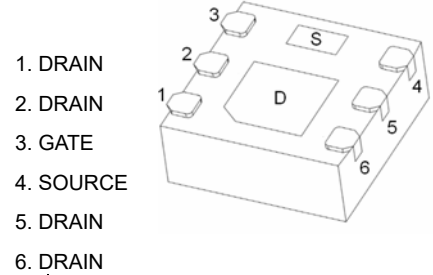


DFNWB2×2-6L Plastic-Encapsulate MOSFETS

CJMP2011 P-Channel Power MOSFET

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
-20 V	15mΩ@-4.5V	-11A
	22mΩ@-2.5V	

DFNWB2×2-6L



DESCRIPTION

The CJMP2011 uses advanced trench technology to provide excellent $R_{DS(on)}$, low gate charge and operation with low gate voltage. This device is suitable for use as a load switching application and a wide variety of other applications.

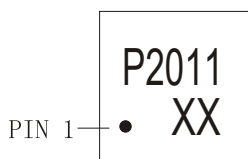
FEATURES

- Advanced trench MOSFET process technology
- Ultra low on-resistance with low gate charge

APPLICATIONS

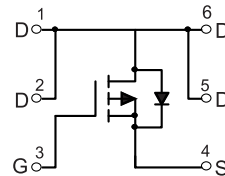
- PWM application
- Load switch
- Battery charge in cellular handset

MARKING



P2011 = Part No.
Solid dot = Pin1 indicator.
XX = Code.

Equivalent Circuit



Maximum ratings ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-20	V
Gate-Source Voltage	V_{GS}	±12	
Drain Current-Continuous	I_D	-11	A
Drain Current-Pulsed (note 1)	I_{DM}	-44	
Power Dissipation (note 4)	P_D	4	W
Thermal Resistance from Junction to Ambient(note 4)	$R_{\theta JA}$	31	$^{\circ}\text{C/W}$
Operation Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~+150	$^{\circ}\text{C}$

MOSFET ELECTRICAL CHARACTERISTICS

$T_a=25^{\circ}\text{C}$ unless otherwise specified

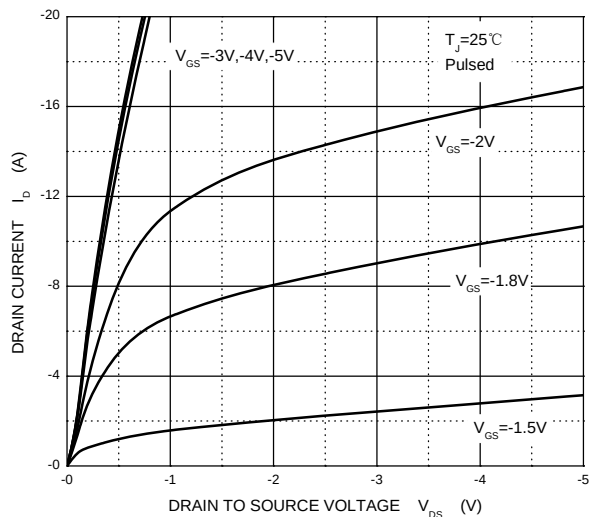
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = -250μA	-20			V
Gate-Body Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μA
On Characteristics (note 2)						
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.45	-0.85	-1.2	V
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-7.2A		15	23.5	mΩ
		V _{GS} =-2.5V, I _D =-6.4A		22	40	
Forward Transconductance	g _{FS}	V _{DS} =-10V, I _D =-7.2A		16		S
Dynamic Characteristics (note 3)						
Input Capacitance	C _{iss}	V _{DS} =-10V,V _{GS} =0V,f =1MHz		2700		pF
Output Capacitance	C _{oss}			680		
Reverse Transfer Capacitance	C _{rss}			590		
Total Gate Charge	Q _g	V _{DS} =-6V,V _{GS} =-4.5V,I _D =-10A		35	48	nC
Gate-Source Charge	Q _{gs}			5		
Gate-Drain Charge	Q _{gd}			10		
SWITCHING CHARACTERISTICS (note 3)						
Turn-on delay time	t _{d(on)}	V _{GEN} =-4.5V,V _{DD} =-10V, I _D =-1A,R _g =10Ω		11		ns
Turn-on rise time	t _r			35		ns
Turn-off delay time	t _{d(off)}			30		ns
Turn-off fall time	t _f			10		ns
Drain-Source Diode Characteristics						
Diode Forward Current	I _S				-11	A
Diode Forward Voltage(note 2)	V _{SD}	V _{GS} =0V, I _{SD} =-1.9A			-1.2	V

Notes:

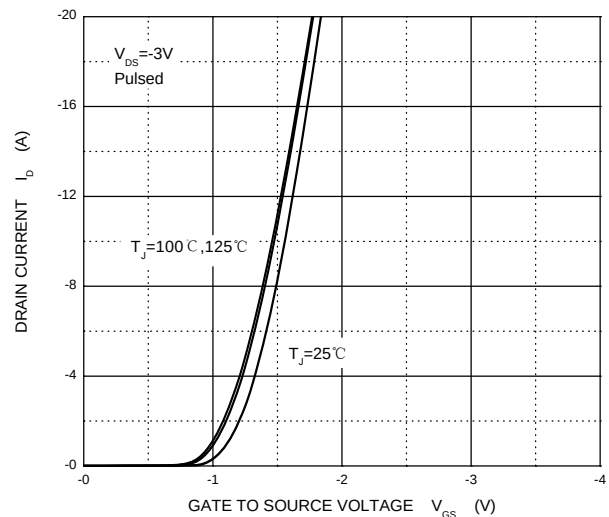
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Pulse Test: Pulse With $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
3. Guaranteed by design, not subject to production testing.
4. The value of $R_{\theta JA}$ is measured with the device mounted on 1 in² FR-4 board with 2oz. Copper, double sides, in a still air environment with $T_A = 25^{\circ}\text{C}$.

Typical Characteristics

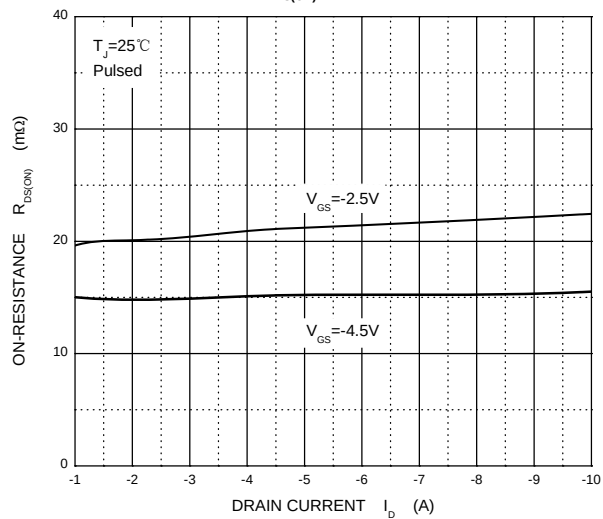
Output Characteristics



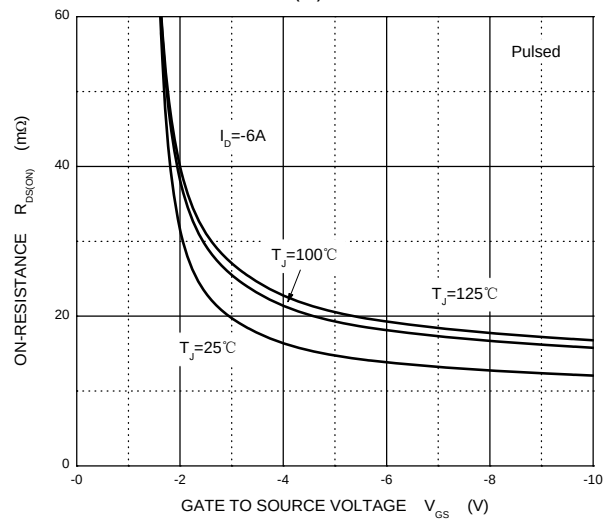
Transfer Characteristics



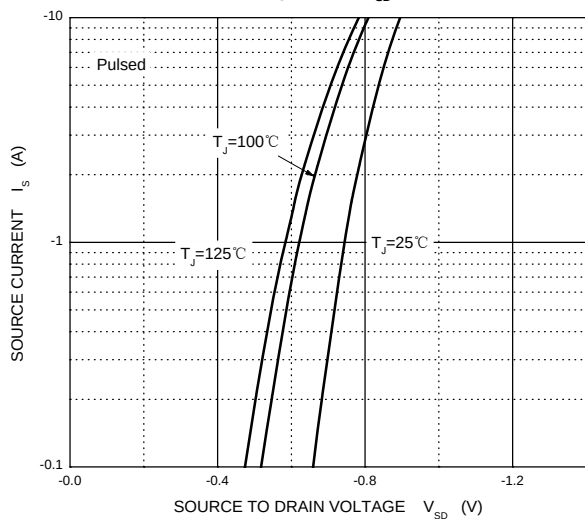
$R_{DS(ON)}$ — I_D



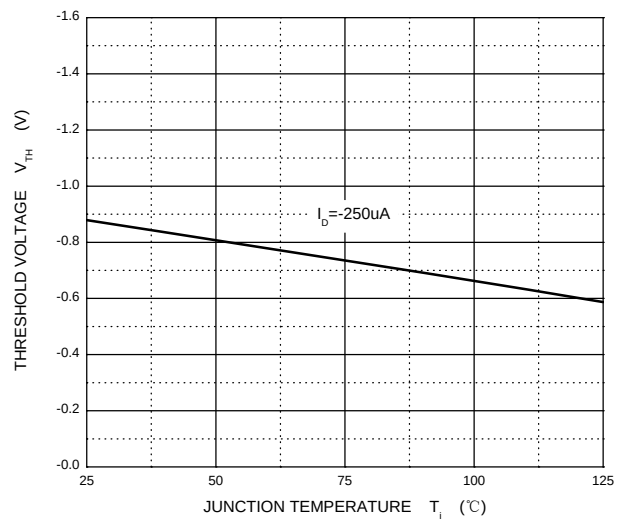
$R_{DS(ON)}$ — V_{GS}



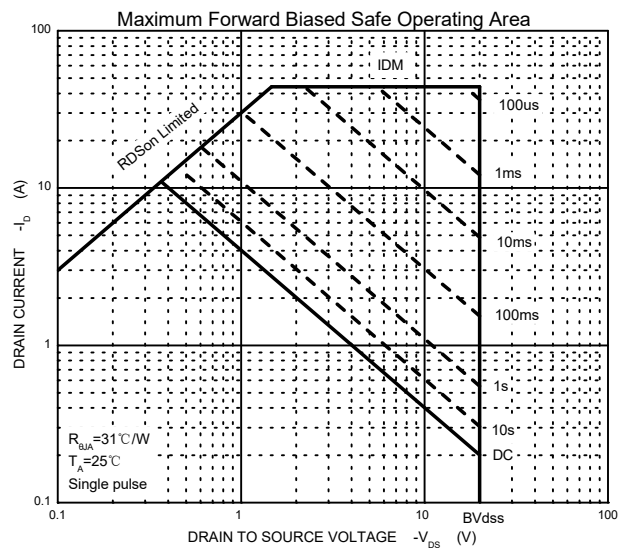
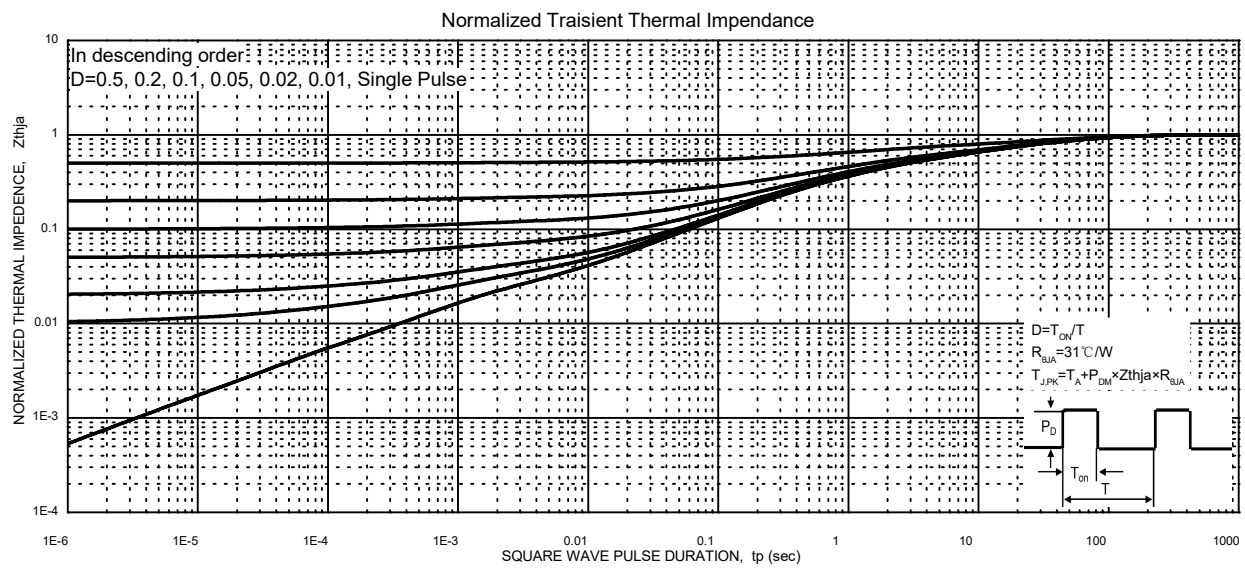
I_S — V_{SD}



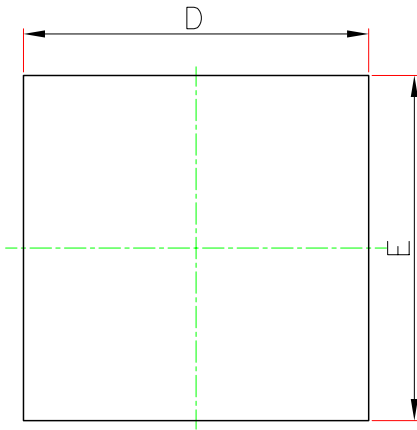
Threshold Voltage



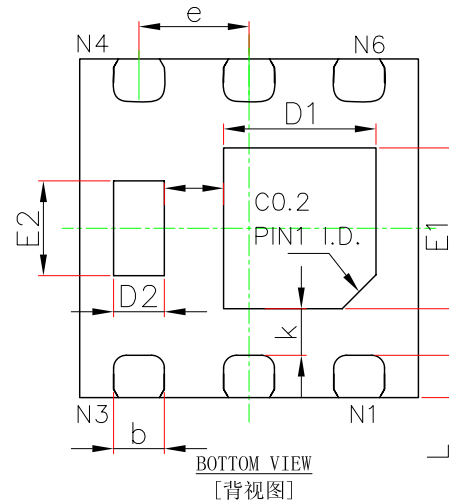
Typical Characteristics



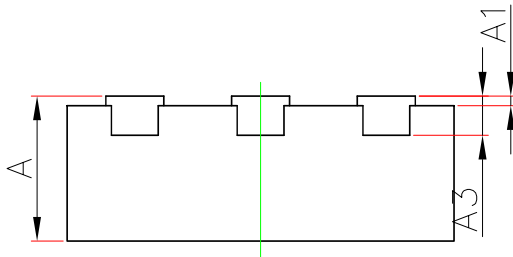
DFNWB2×2-6L-J Package Outline Dimensions



TOP VIEW
[顶视图]



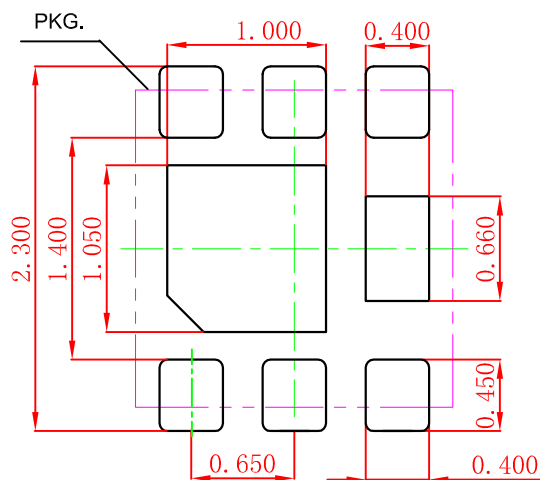
BOTTOM VIEW
[背视图]



SIDE VIEW
[侧视图]

Symbols	Dimensions in Millimeters		Dimensions in Inches	
	Min.	Max.	Min.	Max.
A	0.700	0.800	0.028	0.031
A1	0.000	0.050	0.000	0.002
A3	0.203REF.		0.008REF.	
D	1.900	2.100	0.075	0.083
E	1.900	2.100	0.075	0.083
D1	0.800	1.000	0.031	0.039
E1	0.850	1.050	0.033	0.041
D2	0.200	0.400	0.008	0.016
E2	0.460	0.660	0.018	0.026
b	0.250	0.350	0.010	0.014
e	0.650BSC.		0.026BSC.	
k	0.275REF.		0.011REF.	
k1	0.350REF.		0.014REF.	
L	0.174	0.326	0.007	0.013

DFNWB2×2-6L-J Suggested Pad Layout



Note:

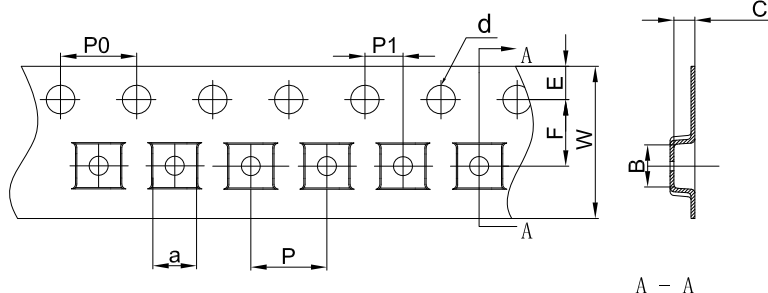
1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.050\text{mm}$.
3. The pad layout is for reference purposes only.

NOTICE

JSCJ reserves the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. JSCJ does not assume any liability arising out of the application or use of any product described herein.

DFNWB2×2-6L Tape and Reel

DFNWB2×2-6L Embossed Carrier Tape

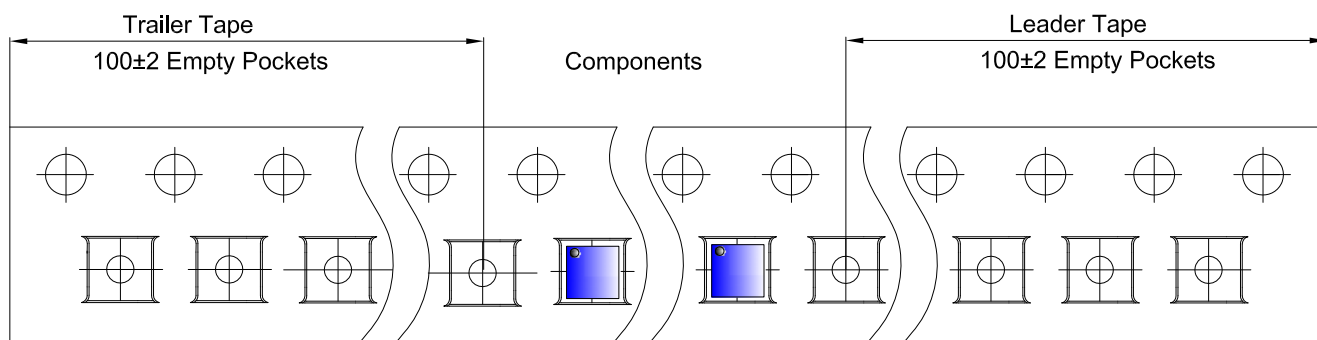


Packaging Description:

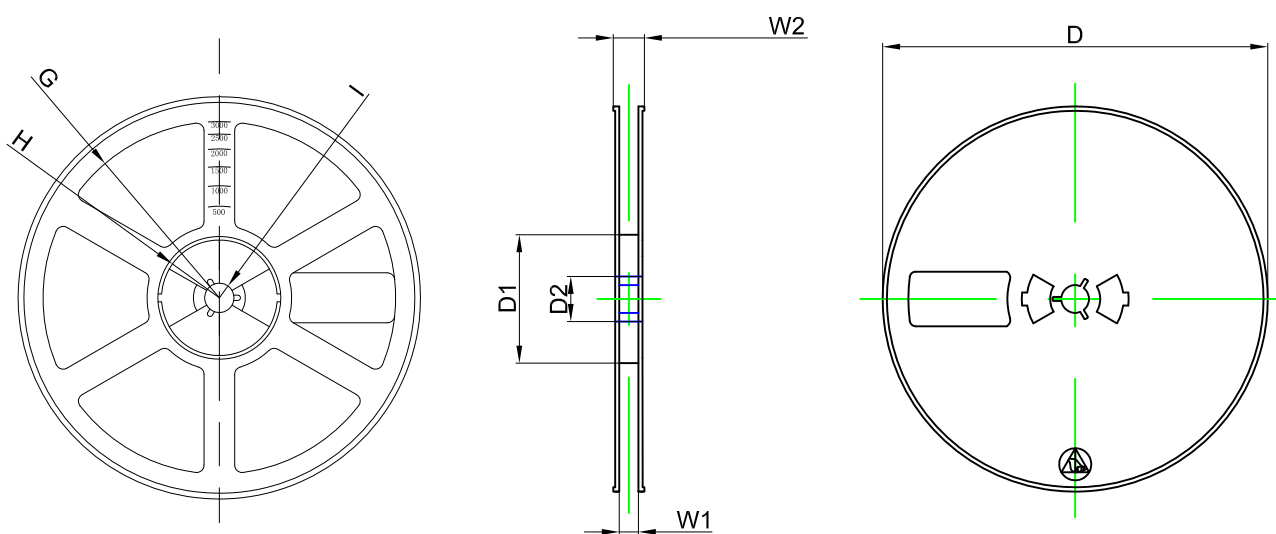
DFNWB2×2-6L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 3,000 units per 7" or 18.0cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
DFNWB2×2-6L	2.30	2.30	1.10	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

DFNWB2×2-6L Tape Leader and Trailer



DFNWB2×2-6L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7"Dia	Ø180.00	60.00	13.00	R78.00	R25.60	R6.50	9.50	13.10

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	